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## 高い放射線耐性を有する半導体素子の開発 Development of semiconductor devices with high-radiation hardness

学術論文（査読あり）

- [1] K. Takakura, V. Puytcha, E. Simoen, A.R. Alioan, U. Peralagu, N. Waldron, B. Parvais, N. Collaert, “Parasitic subthreshold drain current and low frequency noise in GaN/AlGaIn MOSHEMTs,” *Semiconductor Science and Technology* **Volume 36**, p. 024003 (4 pp.) (2020).
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卒業論文

- [1] 鶴田惟月「高信頼性半導体素子の開発」熊本高等専門学校卒業研究論文 2020年.

国際会議

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